

Excellent Integrated System Limited

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Vishay/Siliconix SI7402DN-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com





Si7402DN

Vishay Siliconix

N-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
12	0.0057 at V _{GS} = 4.5 V	20		
	0.0067 at V _{GS} = 2.5 V	18.8		
	0.0085 at V _{GS} = 1.8 V	16.5		

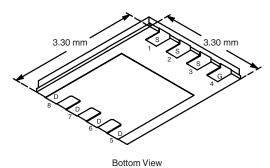
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- Compliant to RoHS Directive 2002/95/EC



RoHS HALOGEN

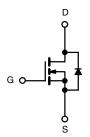
PowerPAK 1212-8



Ordering Information: Si7402DN-T1-E3 (Lead (Pb)-free) Si7402DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- PA Switch, Load Switch and Battery Switch for Portable
- Point-of-Load for 5 V or 3.3 V BUS Stepdown



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	12		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Proin Current /T = 150 °C\8	T _A = 25 °C	I _D	20	13		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		16	10		
Pulsed Drain Current		I _{DM}	50		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	3.2	1.3		
Martin and Branch and A	T _A = 25 °C	P _D	3.8	1.5	W	
Maximum Power Dissipation ^a	T _A = 70 °C		2.4	1.0		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	24	33	°C/W
	Steady State		65	81	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.4	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Datasheet of SI7402DN-T1-E3 - MOSFET N-CH 12V 13A PPAK 1212-8

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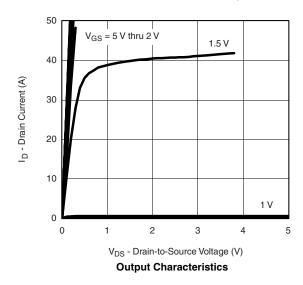


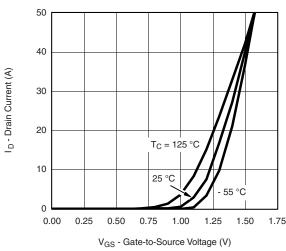
MOSFET SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.45		0.85	٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zana Oata Valtana Busin Oumant	I _{DSS}	V _{DS} = 12 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current		V _{DS} = 12 V, V _{GS} = 0 V, T _J = 55 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	50			Α	
		V _{GS} = 4.5 V, I _D = 20 A		0.0045	0.0057		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 18 \text{ A}$		0.0053	0.0067	Ω	
		$V_{GS} = 1.8 \text{ V}, I_D = 10 \text{ A}$		0.0065	0.0085		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		100		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 3.2 A, V _{GS} = 0 V		0.70	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			36	55		
Gate-Source Charge	Q _{gs}	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		4		nC	
Gate-Drain Charge	Q_{gd}			9.5			
Gate Resistance	R_g			1.8		Ω	
Turn-On Delay Time	t _{d(on)}			35	55		
Rise Time	t _r	V_{DD} = 6 V, R_L = 6 Ω		65	100	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_g = 6 Ω		110	165		
Fall Time	t _f			60	90		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.3 A, dI/dt = 100 A/μs		40	80		

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Transfer Characteristics

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

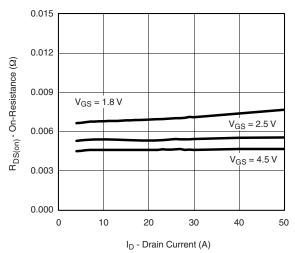




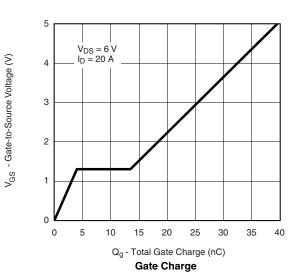
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



S - Source Current (A) 10 T_{.J} = 25 °C

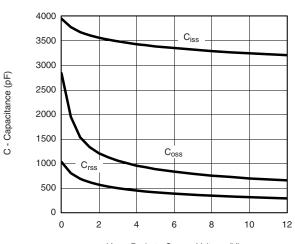
0.4

T_J = 150 °C

V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage

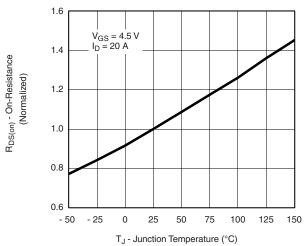
0.8

1.2

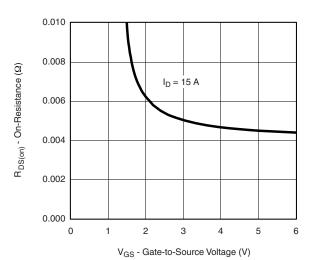


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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0.0

0.2

50

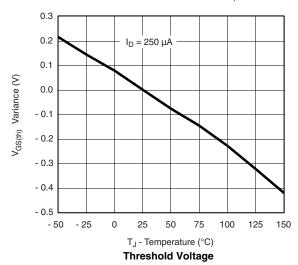


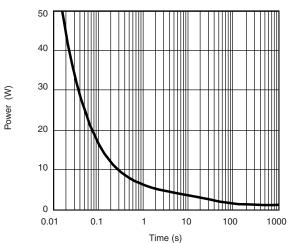
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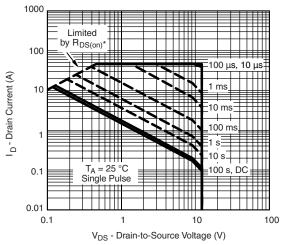
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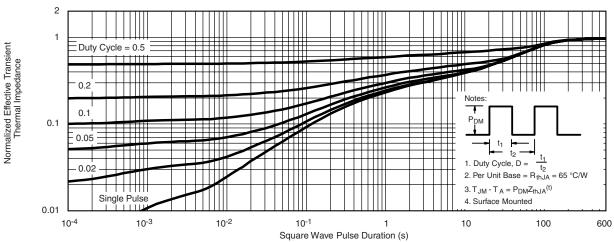




Single Pulse Power, Junction-to-Ambient



 * V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified **Safe Operating Area**



Normalized Thermal Transient Impedance, Junction-to-Ambient

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Datasheet of SI7402DN-T1-E3 - MOSFET N-CH 12V 13A PPAK 1212-8

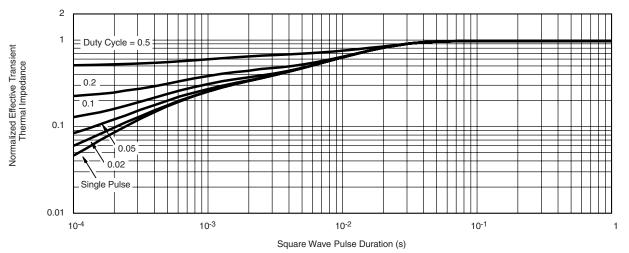
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72646.

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Distributor of Vishay/Siliconix: Excellent Integrated System Limited Datasheet of SI7402DN-T1-E3 - MOSFET N-CH 12V 13A PPAK 1212-8

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